

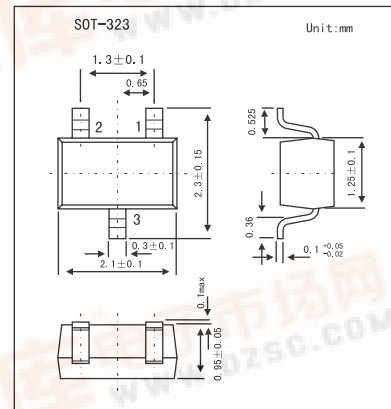
SMD Type Diodes

Silicon Schottky Diode

BAT68-04W, BAT68-05W, BAT68-06W

■ Features

- For mixer applications in VHF/UHF range
- For high-speed switching application



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit
Diode reverse voltage	V _R	8	V
Forward current	I _F	130	mA
Total power dissipation	P _{tot}	150	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C
Junction - soldering point(Note 1)	R _{thJS}	≤ 390	K/W

Note

1. For calculation of R_{thJA} please refer to Application Note Thermal Resistance

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Breakdown voltage	V _(BR)	I _(BR) = 10 μA	8			V
Reverse current	I _R	V _R = 1 V			0.1	μA
		V _R = 1 V, T _A = 60°C			1.2	
Forward voltage	V _F	I _F = 1 mA		318	340	mV
		I _F = 10 mA	340	390	500	
Diode capacitance	C _T	V _R = 0, f = 1 MHz			1	pF
Differential forward resistance	R _F	I _F = 5 mA, f = 10 KHz			10	Ω

■ Marking

Type	BAT68-04W	BAT68-05W	BAT68-06W
Marking	84s	85s	86s